



PATENT  
Attorney Docket No. ASC-049C1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S): Fitzgerald CONFIRMATION NO.: 8754  
SERIAL NO.: 10/774,890 GROUP NO.: 2818  
FILING DATE: February 9, 2004 EXAMINER: Tran, Mai Huong  
TITLE: RELAXED SiGe PLATFORM FOR HIGH SPEED CMOS  
ELECTRONICS AND HIGH SPEED ANALOG CIRCUITS

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. Copies of the patents and publications are enclosed. In accordance with the U.S. Patent Office's partial waiver of the requirement under 37 C.F.R. 1.98 (a)(2)(i), only copies of the foreign patent documents and non-patent publications are enclosed.

**REMARKS**

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

- (1) within three (3) months of the **filing date** of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the **date of entry of the national stage** as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the **first Office action** on the merits, or before the mailing of a **first Office action** after the filing of a request for continued examination under 37 C.F.R. 1.114; or
- (2) after the period defined in (1) but before the mailing date of a **final action** or a **notice of allowance** under 37 C.F.R. 1.311, and
- the requisite Statement is below, OR

- the requisite fee under 37 C.F.R. 1.17(p), namely **\$180.00**, is included herein, or
- (3) after the mailing date of a **final action or notice of allowance** but before the payment of the **issue fee**, AND
  - the requisite Statement is below, AND
  - the requisite petition fee under 37 C.F.R. 1.17(p), namely **\$180.00** is included herein.

Applicant wishes to inform the Examiner about the following co-pending patent applications and Office actions issued therein:

- 1) U.S. Serial No. 09/611,024 (Docket No. ASC-023) filed on 06/07/2000, by Fitzgerald;
- 2) U.S. Serial No. 10/611,739 (Docket No. ASC-044C1) filed on 07/01/2003, by Fitzgerald *et al.*;
- 3) U.S. Serial No. 10/802,185 (Docket No. ASC-025DVC1) filed on 03/17/2004, by Cheng *et al.*;
- 4) U.S. Serial No. 10/802,186 (Docket No. ASC-025DV2C1) filed on 03/17/2004, by Cheng *et al.*;
- 5) U.S. Serial No. 10/826,156 (Docket No. ASC-023C2) filed on 04/16/2004, by Fitzgerald;
- 6) U.S. Serial No. 10/854,556 (Docket No. ASC-054C1), filed May 26, 2004, by Fitzgerald;
- 7) U.S. Serial No. 09/884,817 (Docket No. ASC-043), filed June 19, 2001 by Fitzgerald *et al.*;
- 8) U.S. Serial No. 10/022,689 (Docket No. ASC-023DVC2), filed December 17, 2001 by Fitzgerald;
- 9) U.S. Serial No. 09/906,534 (Docket No. ASC-054), filed July 16, 2001 by Fitzgerald;
- 10) U.S. Serial No. 09/906,533 (Docket No. ASC-052), filed July 16, 2001 by Fitzgerald;
- 11) U.S. Serial No. 10/005,274 (Docket No. ASC-043CP), filed December 4, 2001 by Fitzgerald *et al.*;
- 12) U.S. Serial No. 10/116,559 (Docket No. ASC-026), filed April 4, 2002 by Cheng *et al.*;
- 13) U.S. Serial No. 10/172,542 (Docket No. ASC-057), filed June 14, 2002 by Hammond *et al.*;
- 14) U.S. Serial No. 10/266,399 (Docket No. ASC-043C1), filed October 8, 2002 by Fitzgerald *et al.*;
- 15) U.S. Serial No. 10/253,361 (Docket No. ASC-018), filed September 24, 2002 by Braithwaite *et al.*;
- 16) U.S. Serial No. 10/389,003 (Docket No. ASC-019), filed March 14, 2003 by Fitzgerald *et al.*;
- 17) U.S. Serial No. 10/264,935 (Docket No. ASC-008), filed October 4, 2002 by Lochtefeld *et al.*;
- 18) U.S. Serial No. 10/456,103 (Docket No. ASC ASC-008C), filed June 6, 2003 by Lochtefeld *et al.*;
- 19) U.S. Serial No. 10/456,708 (Docket No. ASC ASC-008B), filed June 6, 2003 by Lochtefeld; and
- 20) U.S. Serial No. 10/625,018 (Docket No. ASC-043C2), filed by Fitzgerald *et al.*.

Information Disclosure Statement

Serial No. 10/774,890

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It is respectfully requested that the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.

Respectfully submitted,

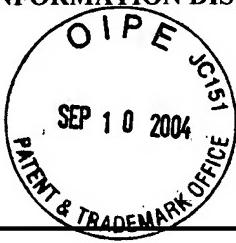
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<b>FORM PTO - 1449</b> <b>INFORMATION DISCLOSURE STATEMENT</b> 				ATTY DOCKET NO.: ASC-049C1 APPLICANT: Fitzgerald SERIAL NO.: 10/774,890 FILING DATE: February 9, 2004 EXAMINER: Tran, Mai Huong C. GROUP: 2818			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A1	2001/0003364	06/14/2001	Sugawara <i>et al.</i>			
	A2	2002/0024395	02/28/2002	Akatsuka <i>et al.</i>			
	A3	2002/0043660	04/18/2002	Yamazaki <i>et al.</i>			
	A4	2002/0084000	07/04/2002	Fitzgerald			
	A5	2002/0096717	07/25/2002	Chu <i>et al.</i>			
	A6	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i>			
	A7	2002/0123167	09/05/2002	Fitzgerald			
	A8	2002/0123183	09/05/2002	Fitzgerald			
	A9	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i>			
	A10	2002/0168864	11/14/2002	Cheng <i>et al.</i>			
	A11	2003/0003679	01/02/2003	Doyle <i>et al.</i>			
	A12	2003/0013323	01/16/2003	Hammond <i>et al.</i>			
	A13	2003/0034529	02/20/2003	Fitzgerald <i>et al.</i>			
	A14	2003/0057439	03/27/2003	Fitzgerald			
	A15	2003/0102498	06/05/2003	Braithwaite <i>et al.</i>			
	A16	2003/0199126	10/23/2003	Chu <i>et al.</i>			
	A17	2003/0203600	10/30/2003	Chu <i>et al.</i>			
	A18	2003/0215990	11/20/2003	Fitzgerald <i>et al.</i>			
	A19	2003/0218189	11/27/2003	Christiansen			
	A20	2003/0227057	12/01/2003	Lochtefeld <i>et al.</i>			
	A21	2004/0005740	01/01/2004	Lochtefeld <i>et al.</i>			
	A22	2004/0014304	01/22/2004	Bhattacharyya			
	A23	2004/0031979	02/19/2004	Lochtefeld			06/06/2003
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			

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	A24	2004/0041210	03/04/2004	Mouli			09/02/2003
	A25	2004/0075149	04/22/2004	Fitzgerald <i>et al.</i>			07/23/2003
	A26	4,010,045	03/01/1977	Ruehrwein			
	A27	4,710,788	12/01/1987	Dambkes <i>et al.</i>			
	A28	4,987,462	01/22/1991	Kim <i>et al.</i>			
	A29	4,990,979	02/05/1991	Otto			
	A30	4,997,776	03/05/1991	Harame <i>et al.</i>			
	A31	5,013,681	05/07/1991	Godbey <i>et al.</i>			
	A32	5,155,571	10/13/1992	Wang <i>et al.</i>			
	A33	5,166,084	11/24/1992	Pfiester			
	A34	5,177,583	01/05/1993	Endo <i>et al.</i>			
	A35	5,202,284	04/13/1993	Kamins <i>et al.</i>			
	A36	5,207,864	05/04/1993	Bhat <i>et al.</i>			
	A37	5,208,182	05/04/1993	Narayan <i>et al.</i>			
	A38	5,212,110	05/18/1993	Pfiester <i>et al.</i>			
	A39	5,221,413	06/22/1993	Brasen <i>et al.</i>			
	A40	5,240,876	08/34/1993	Gaul <i>et al.</i>			
	A41	5,241,197	08/31/1993	Murakami <i>et al.</i>			
	A42	5,250,445	10/05/1993	Bean <i>et al.</i>			
	A43	5,285,086	02/08/1994	Fitzgerald			
	A44	5,291,439	03/01/1994	Kauffmann <i>et al.</i>			
	A45	5,298,452	03/29/1994	Meyerson			
	A46	5,310,451	05/10/1994	Tejwani <i>et al.</i>			
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A47	5,316,958	05/31/1994	Meyerson			
	A48	5,346,848	09/13/1994	Grupen-Shemansky <i>et al.</i>			
	A49	5,374,564	12/20/1994	Bruel			
	A50	5,399,522	03/21/1995	Ohori			
	A51	5,413,679	05/09/1995	Godbey			
	A52	5,424,243	06/13/1995	Takasaki			
	A53	5,426,069	06/20/1995	Selvakumar <i>et al.</i>			
	A54	5,426,316	06/20/1995	Mohammad			
	A55	5,442,205	08/15/1995	Brasen <i>et al.</i>			
	A56	5,461,243	10/24/1995	Ek <i>et al.</i>			
	A57	5,461,250	10/24/1995	Burghartz <i>et al.</i>			
	A58	5,462,883	10/31/1995	Dennard <i>et al.</i>			
	A59	5,476,813	12/19/1995	Naruse			
	A60	5,479,033	12/26/1995	Baca <i>et al.</i>			
	A61	5,484,664	01/16/1996	Kitahara <i>et al.</i>			
	A62	5,523,243	06/04/1996	Mohammad			
	A63	5,523,592	06/04/1996	Nakagawa <i>et al.</i>			
	A64	5,534,713	07/09/1996	Ismail <i>et al.</i>			
	A65	5,536,361	07/16/1996	Kondo <i>et al.</i>			
	A66	5,540,785	07/30/1996	Dennard <i>et al.</i>			
	A67	5,572,043	11/05/1996	Shimizu <i>et al.</i>			
	A68	5,596,527	01/21/1997	Tomioka <i>et al.</i>			
	A69	5,617,351	04/01/1997	Bertin <i>et al.</i>			
<b>EXAMINER</b>				<b>DATE CONSIDERED</b> 438			

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	A70	5,630,905	05/20/1997	Lynch <i>et al.</i>			
	A71	5,659,187	08/19/1997	Legoues <i>et al.</i>			
	A72	5,683,934	11/04/1997	Candelaria			
	A73	5,698,869	12/16/1997	Yoshimi <i>et al.</i>			
	A74	5,714,777	02/03/1998	Ismail <i>et al.</i>			
	A75	5,728,623	03/17/1998	Mori			
	A76	5,739,567	04/14/1998	Wong			
	A77	5,759,898	06/02/1998	Ek <i>et al.</i>			
	A78	5,777,347	07/07/1998	Bartelink			
	A79	5,786,612	07/28/1998	Otani <i>et al.</i>			
	A80	5,786,614	07/28/1998	Chuang <i>et al.</i>			
	A81	5,792,679	08/11/1998	Nakato			
	A82	5,808,344	09/15/1998	Ismail <i>et al.</i>			
	A83	5,847,419	12/08/1998	Imai <i>et al.</i>			
	A84	5,877,070	03/02/1999	Goesele <i>et al.</i>			
	A85	5,891,769	04/06/1999	Liaw <i>et al.</i>			
	A86	5,906,708	05/25/1999	Robinson <i>et al.</i>			
	A87	5,906,951	05/25/1999	Chu <i>et al.</i>			
	A88	5,912,479	06/15/1999	Mori <i>et al.</i>			
	A89	5,943,560	08/24/1999	Chang <i>et al.</i>			
	A90	5,963,817	10/05/1999	Chu <i>et al.</i>			
	A91	5,966,622	10/12/1999	Levine <i>et al.</i>			
	A92	5,998,807	12/07/1999	Lustig <i>et al.</i>			
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			

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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A93	6,013,134	01/11/2000	Chu <i>et al.</i>			
	A94	6,030,887	02/29/2000	Desai <i>et al.</i>			
	A95	6,030,889	02/29/2000	Aulicino <i>et al.</i>			
	A96	6,033,974	03/07/2000	Henley <i>et al.</i>			
	A97	6,033,995	03/07/2000	Muller			
	A98	6,058,044	05/02/2000	Sugiura <i>et al.</i>			
	A99	6,059,895	05/09/2000	Chu <i>et al.</i>			
	A100	6,074,919	06/13/2000	Gardner <i>et al.</i>			
	A101	6,096,590	08/01/2000	Chan <i>et al.</i>			
	A102	6,103,559	08/15/2000	Gardner <i>et al.</i>			
	A103	6,107,653	08/22/2000	Fitzgerald			
	A104	6,111,267	08/29/2000	Fischer <i>et al.</i>			
	A105	6,117,750	09/12/2000	Bensahel <i>et al.</i>			
	A106	6,130,453	10/10/2000	Mei <i>et al.</i>			
	A107	6,133,799	10/17/2000	Favors <i>et al.</i>			
	A108	6,140,687	10/31/2000	Shimomura <i>et al.</i>			
	A109	6,143,636	11/07/2000	Forbes <i>et al.</i>			
	A110	6,153,495	11/28/2000	Kub <i>et al.</i>			
	A111	6,154,475	11/28/2000	Soref <i>et al.</i>			
	A112	6,160,303	12/12/2000	Fattaruso			
	A113	6,162,688	12/19/2000	Gardner <i>et al.</i>			
	A114	6,184,111	02/06/2001	Henley <i>et al.</i>			
	A115	6,191,007	02/20/2001	Matsui <i>et al.</i>			
EXAMINER				DATE CONSIDERED			

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<b>U.S. PATENT DOCUMENTS</b>							
<b>EXAM. INIT.</b>		<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>NAME</b>	<b>CLASS</b>	<b>SUB CLASS</b>	<b>FILING DATE IF APPROPRIATE</b>
	A116	6,191,432	02/20/2001	Sugiyama <i>et al.</i>			
	A117	6,194,722	02/27/2001	Fiorini <i>et al.</i>			
	A118	6,204,529	03/20/2001	Lung <i>et al.</i>			
	A119	6,207,977	03/27/2001	Augusto			
	A120	6,210,988	04/03/2001	Howe <i>et al.</i>			
	A121	6,218,677	04/17/2001	Broekaert			
	A122	6,232,138	05/15/2001	Fitzgerald <i>et al.</i>			
	A123	6,235,567	05/22/2001	Huang			
	A124	6,242,324	06/05/2001	Kub <i>et al.</i>			
	A125	6,249,022	06/19/2001	Lin <i>et al.</i>			
	A126	6,251,755	06/26/2001	Furukawa <i>et al.</i>			
	A127	6,261,929	07/17/2001	Gehrke <i>et al.</i>			
	A128	6,266,278	07/24/2001	Harari <i>et al.</i>			
	A129	6,271,551	08/07/2001	Schmitz <i>et al.</i>			
	A130	6,271,726	08/07/2001	Fransis <i>et al.</i>			
	A131	6,291,321	09/18/2001	Fitzgerald			
	A132	6,313,016	11/06/2001	Kibbel <i>et al.</i>			
	A133	6,316,301	11/13/2001	Kant			
	A134	6,323,108	11/27/2001	Kub <i>et al.</i>			
	A135	6,329,063	12/11/2001	Lo <i>et al.</i>			
	A136	6,335,546	01/01/2002	Tsuda <i>et al.</i>			
	A137	6,339,232	01/15/2002	Takagi			
	A138	6,350,993	02/26/2002	Chu <i>et al.</i>			
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A139	6,352,909	03/05/2002	Usenko				
	A140	6,368,733	04/09/2002	Nishinaga				
	A141	6,372,356	04/16/2002	Thornton <i>et al.</i>				
	A142	6,372,593	04/16/2002	Hattori <i>et al.</i>				
	A143	6,399,970	06/04/2002	Kubo <i>et al.</i>				
	A144	6,403,975	06/11/2002	Brunner <i>et al.</i>				
	A145	6,407,406	06/18/2002	Tezuka				
	A146	6,420,937	07/16/2002	Akatsuka <i>et al.</i>				
	A147	6,425,951	07/30/2002	Chu <i>et al.</i>				
	A148	6,429,061	08/06/2002	Rim				
	A149	6,521,041	02/18/2003	Wu <i>et al.</i>				
	A150	6,524,935	02/25/2003	Canaperi <i>et al.</i>				
	A151	6,555,839	04/29/2003	Fitzgerald				
	A152	6,573,126	06/03/2003	Cheng <i>et al.</i>				
	A153	6,583,015	06/24/2003	Fitzgerald <i>et al.</i>				
	A154	6,593,191	07/15/2003	Fitzgerald				
	A155	6,593,641	07/15/2003	Fitzgerald				
	A156	6,602,613	08/05/2003	Fitzgerald				
	A157	6,603,156	08/05/2003	Rim				
	A158	6,646,322	11/11/2003	Fitzgerald				
	A159	6,649,480	11/18/2003	Fitzgerald <i>et al.</i>				
	A160	6,677,192	01/13/2004	Fitzgerald				
	A161	6,703,144	03/09/2004	Fitzgerald			03/18/2003	
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A162	6,703,688	03/09/2004	Fitzgerald				07/16/2001	
	A163	6,709,903	03/23/2004	Christiansen				04/30/2003	
	A164	6,713,326	03/30/2004	Cheng <i>et al.</i>				03/04/2003	
	A165	6,723,661	04/20/2004	Fitzgerald				07/16/2001	
	A166	6,724,008	04/20/2004	Fitzgerald				07/16/2001	
	A167	6,730,551	05/04/2004	Lee <i>et al.</i>				08/02/2002	
	A168	6,737,670	05/18/2004	Cheng <i>et al.</i>				03/07/2003	
	A169	6,750,130	06/15/2004	Fitzgerald				01/07/2001	
<b>FOREIGN PATENT DOCUMENTS</b>									
EXAM .INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B1	41 01 167	07/23/1992	DE				N	Y (Abstract only)
	B2	0 514 018	11/19/1992	EP				N	Y
	B3	0 587 520	03/16/1994	EP				N	Y
	B4	0 683 522	11/22/1995	EP				N	Y
	B5	0 828 296	03/11/1998	EP				N	Y
	B6	0 829 908	03/18/1998	EP				N	Y
	B7	0 838 858	04/29/1998	EP				N	Y (Abstract only)
	B8	1 020 900	07/19/2000	EP				N	Y
	B9	1 174 928	01/23/2002	EP				N	Y
	B10	2 701 599	09/01/1993	FR				Y	Y
	B11	2 342 777	04/19/2000	GB				N	Y
	B12	61/141116	06/28/1986	JP				N	Y (Abstract only)
	B13	2/210816	08/22/1990	JP				N	Y (Abstract only)
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	B14	3/036717	02/18/1991	JP				N	Y
	B15	4-307974	10/30/1992	JP				N	Y (Abstract only)
	B16	5-166724	07/23/1993	JP				N	Y (Abstract only)
	B17	6-177046	06/24/1994	JP				N	Y (Abstract only)
	B18	6-244112	09/02/1994	JP				Y	Y
	B19	6-252046	09/09/1994	JP				Y	Y
	B20	7-094420	04/07/1995	JP				N	Y (Abstract only)
	B21	7-106446	04/21/1995	JP				Y	Y
	B22	7-240372	09/12/1995	JP				Y	Y
	B23	10-270685	10/09/1998	JP				N	Y
	B24	11-233744	08/27/1999	JP				N	Y (Abstract only)
	B25	2000-021783	01/21/2000	JP				N	Y
	B26	2000-031491	01/28/2000	JP				Y	Y
	B27	2001-319935	11/16/2001	JP				N	Y
	B28	2002-076334	03/15/2002	JP				N	Y
	B29	2002-164520	06/07/2002	JP				N	Y
	B30	2002-289533	10/04/2002	JP				N	Y
	B31	98/59365	12/30/1998	WO				N	Y
	B32	99/53539	10/21/1999	WO				N	Y
	B33	00/48239	08/17/2000	WO				N	Y
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	B34	00/54338	09/14/2000	WO				N	Y
	B35	01/22482	03/29/2001	WO				N	Y
	B36	01/54202	07/26/2001	WO				N	Y
	B37	01/93338	12/06/2001	WO				N	Y
	B38	01/99169	12/27/2001	WO				N	Y
	B39	02/13262	02/14/2002	WO				N	Y
	B40	02/15244	02/21/2002	WO				N	Y
	B41	02/27783	04/04/2002	WO				N	Y
	B42	02/47168	06/13/2002	WO				N	Y
	B43	02/071488	09/12/2002	WO				N	Y
	B44	02/071491	09/12/2002	WO				N	Y
	B45	02/071495	09/12/2002	WO				N	Y
	B46	02/082514	10/17/2002	WO				N	Y
	B47	04/006311	01/15/2004	WO				N	Y
	B48	04/006327	01/15/2004	WO				N	Y
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	C2	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," Ph.D. Thesis, Massachusetts Institute of Technology, Department of Electrical Engineering and Computer Science (June 30, 1999), pp.1-154.							
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	C4	Barradas <i>et al.</i> , "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMO transistors," <u>Modern Physics Letters B</u> , Vol. 15, No. 28-29 (December 2001), abstract.							
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	C6	Bouillon <i>et al.</i> , "Search for the optimal channel architecture for 0.18/0.12 µm bulk CMOS experimental study," IEEE, (1996), pp. 21.2.1-21.2.4.							
	C7	Bruel <i>et al.</i> , "@SMART CUT: A Promising New SOI Material Technology," Proceedings of the 1995 IEEE International SOI Conference (October 1995), pp. 178-179.							
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<b>OTHER ART, JOURNAL ARTICLES, ETC.</b>									
EXAM. INIT.	<b>OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)</b>								
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